

Silicon Carbide (SiC) Schottky Diode – EliteSiC, 10 A, 650 V, D1, DPAK

FFSD1065A

Description

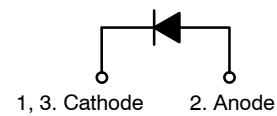
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

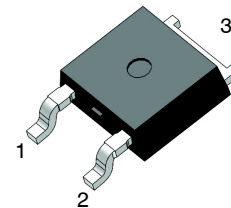
- Max Junction Temperature 175°C
- Avalanche Rated 64 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- This Device is Pb-Free, Halogen Free/BFR Free and RoHS Compliant

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

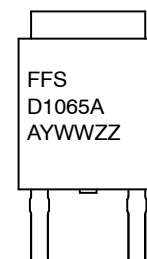


Schottky Diode



DPAK
 CASE 369AS

MARKING DIAGRAM



FFSD1065A	= Specific Device Code
A	= Assembly Site
YWW	= Date Code (Year & Week)
ZZ	= Lot Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FFSD1065A

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Rating	Parameter	FFSD1065A	Unit
V _{RRM}	Peak Repetitive Reverse Voltage		650	V
E _{AS}	Single Pulse Avalanche Energy (Note 1)		64	mJ
I _F	Continuous Rectified Forward Current @ T _C < 158°C		10	A
	Continuous Rectified Forward Current @ T _C < 135°C		18	
I _{F,MAX}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	760	A
		T _C = 150°C, 10 μs	740	A
I _{F,SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, tp = 8.3 ms	56	A
I _{F,RM}	Repetitive Forward Surge Current	Half-Sine Pulse, tp = 8.3 ms	34	A
P _{tot}	Power Dissipation	T _C = 25°C	150	W
		T _C = 150°C	25	W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to + 175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R _{θJC}	Thermal Resistance, Junction to Case, Max.	1.0	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

V _F	Forward Voltage	I _F = 10 A, T _C = 25°C	-	1.50	1.75	V
		I _F = 10 A, T _C = 125°C	-	1.6	2.0	
		I _F = 10 A, T _C = 175°C	-	1.72	2.4	
I _R	Reverse Current	V _R = 650 V, T _C = 25°C	-	-	200	μA
		V _R = 650 V, T _C = 125°C	-	-	400	
		V _R = 650 V, T _C = 175°C	-	-	600	
Q _C	Total Capacitive Charge	V = 400 V	-	34	-	nC
C	Total Capacitance	V _R = 1 V, f = 100 kHz	-	575	-	pF
		V _R = 200 V, f = 100 kHz	-	62	-	
		V _R = 400 V, f = 100 kHz	-	47	-	

1. E_{AS} of 64 mJ is based on starting T_J = 25°C; L = 0.5 mH, I_{AS} = 16 A, V = 50 V.

ORDERING INFORMATION

Device	Marking	Package	Reel Size [†]	Tape Width	Quantity
FFSD1065A	FFSD1065A	DPAK	13"	N/A	2500

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

TYPICAL CHARACTERISTICS
($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

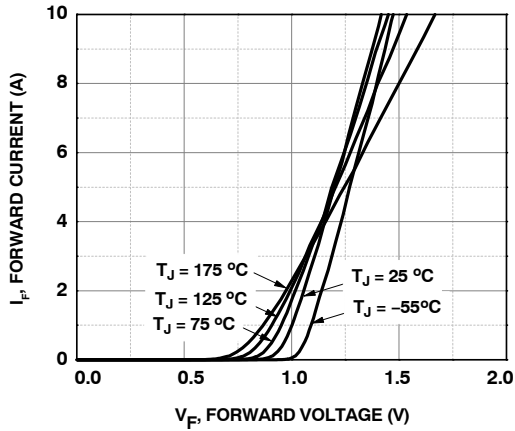


Figure 1. Forward Characteristics

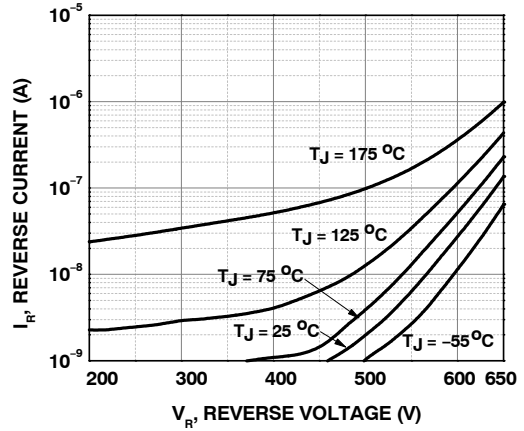


Figure 2. Reverse Characteristics

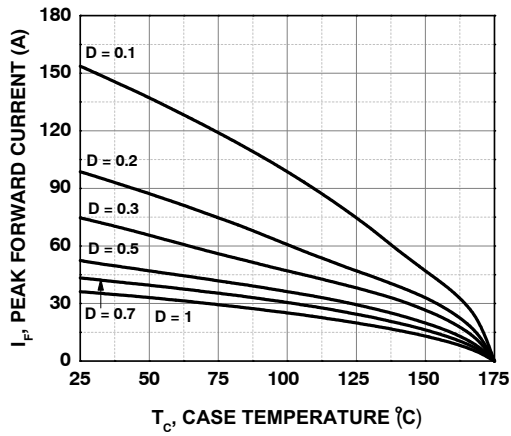


Figure 3. Current Derating

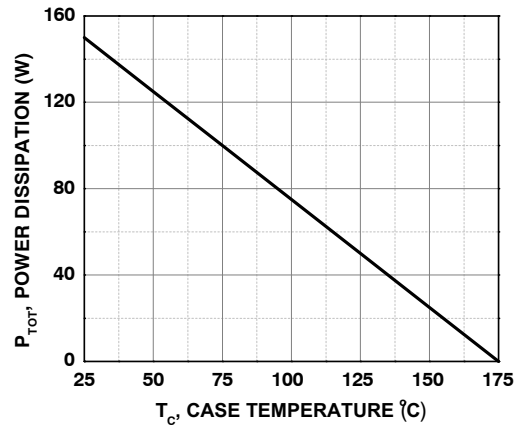


Figure 4. Power Derating

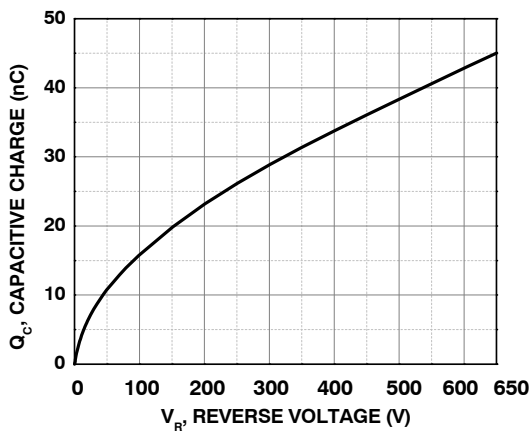


Figure 5. Capacitive Charge vs. Reverse Voltage

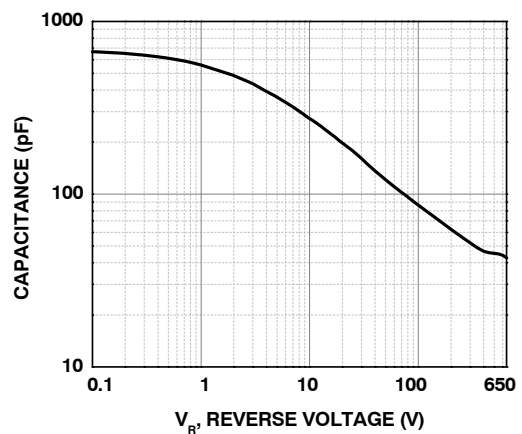


Figure 6. Capacitance vs. Reverse Voltage

FFSD1065A

TYPICAL CHARACTERISTICS (CONTINUED)

($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

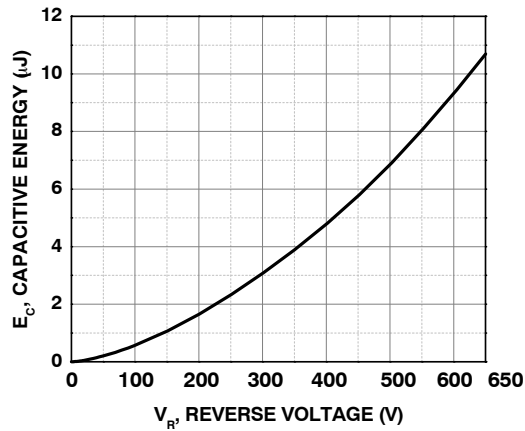


Figure 7. Capacitance Stored Energy

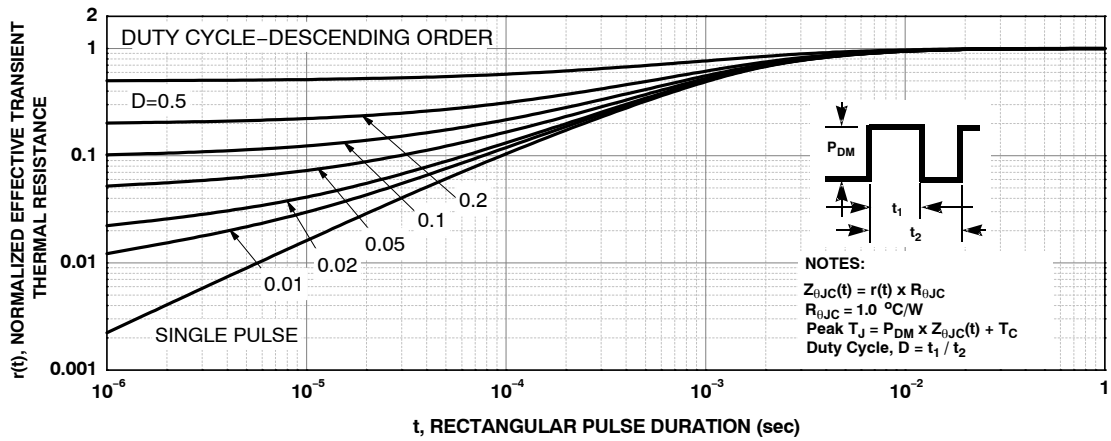


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

$L = 0.5 \text{ mH}$
 $R < 0.1 \Omega$
 $V_{DD} = 50 \text{ V}$
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)} / (V_{R(AVL)} - V_{DD})]$
 $Q1 = \text{IGBT (} BV_{CES} > \text{DUT } V_{R(AVL)} \text{)}$

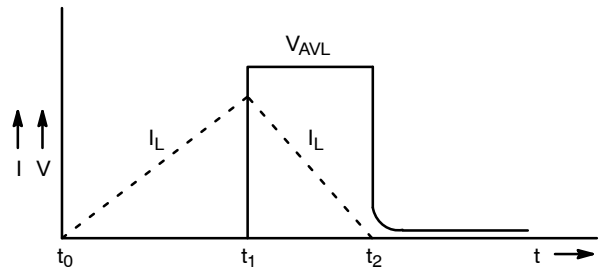
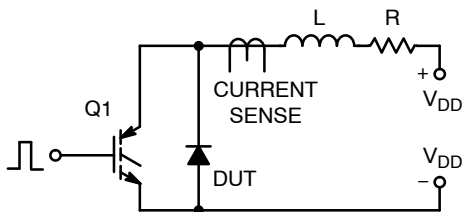
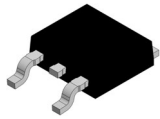


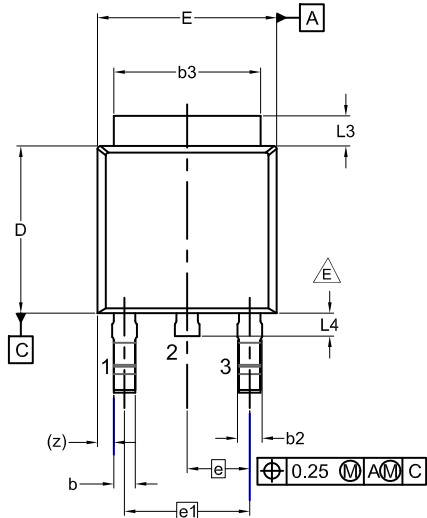
Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

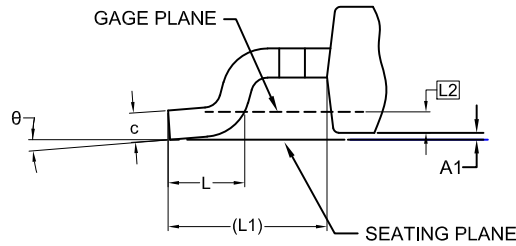


DPAK3 (TO-252 3 LD) CASE 369AS ISSUE A

DATE 28 SEP 2022

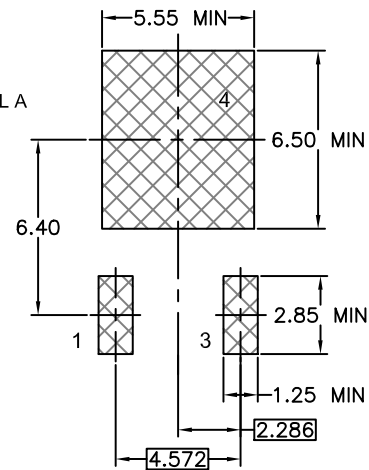
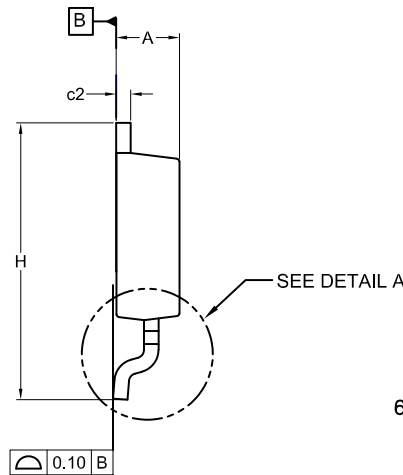
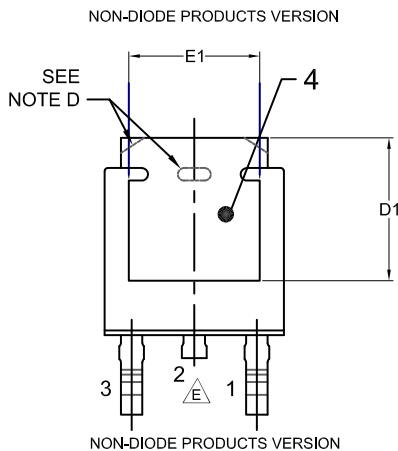


- NOTES: UNLESS OTHERWISE SPECIFIED
 A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
 B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
 D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
 E) FOR DIODE PRODUCTS, L4 IS 0.25 MM MAX.
 F) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
 G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.



DETAIL A
(ROTATED -90°)
SCALE: 12X

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.18	2.29	2.39
A1	0.00	-	0.127
b	0.64	0.77	0.89
b2	0.76	0.95	1.14
b3	5.21	5.34	5.46
c	0.45	0.53	0.61
c2	0.45	0.52	0.58
D	5.97	6.10	6.22
D1	5.21	-	-
E	6.35	6.54	6.73
E1	4.32	-	-
e	2.286 BSC		
e1	4.572 BSC		
H	9.40	9.91	10.41
L	1.40	1.59	1.78
L1	2.90 REF		
L2	0.51 BSC		
L3	0.89	1.08	1.27
L4	-	-	1.02
θ	0°	--	10°



GENERIC MARKING DIAGRAM*



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

LAND PATTERN RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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